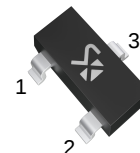


PNP Silicon Epitaxial Planar Transistor

Features

- For switching and amplifier applications.
- Especially suitable for AF-driver stages and low power outputstages.

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

MARKING : 591

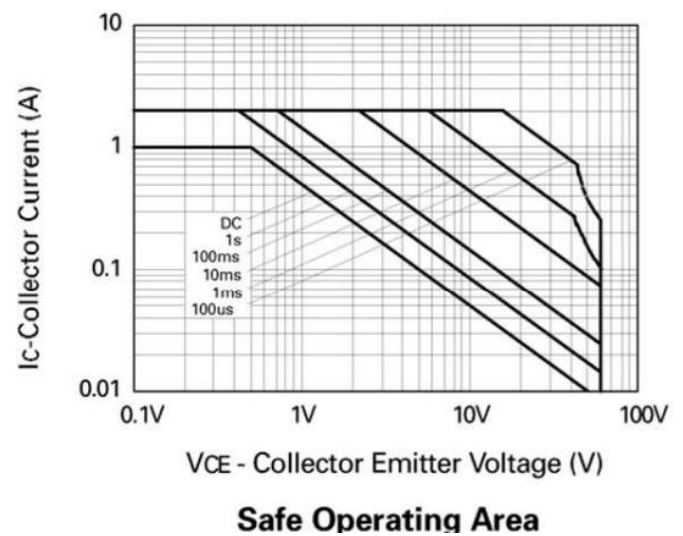
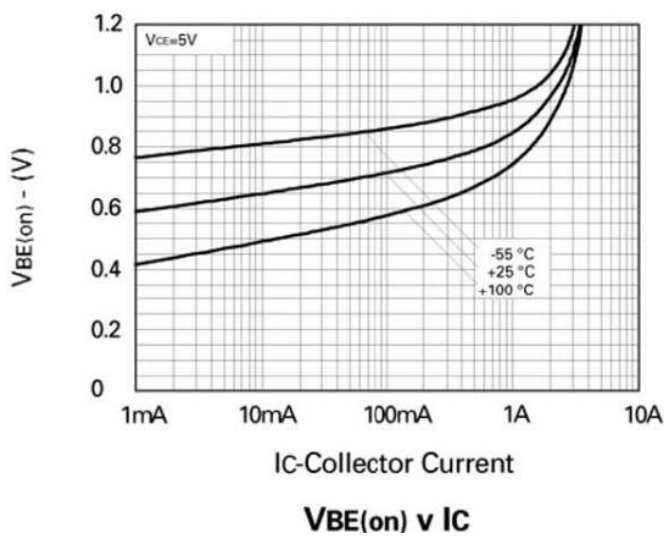
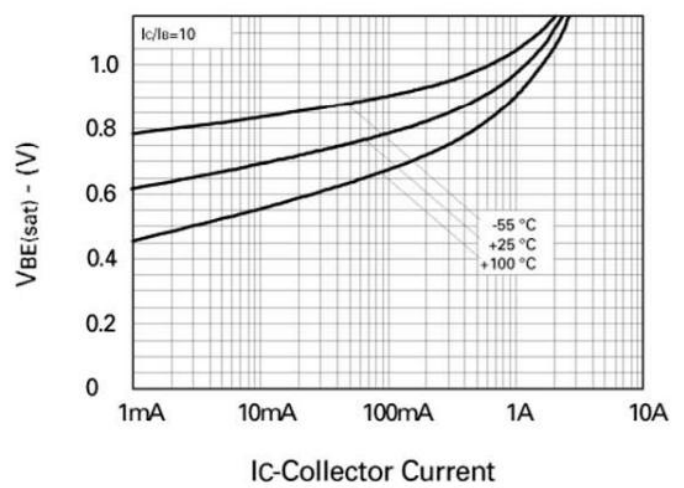
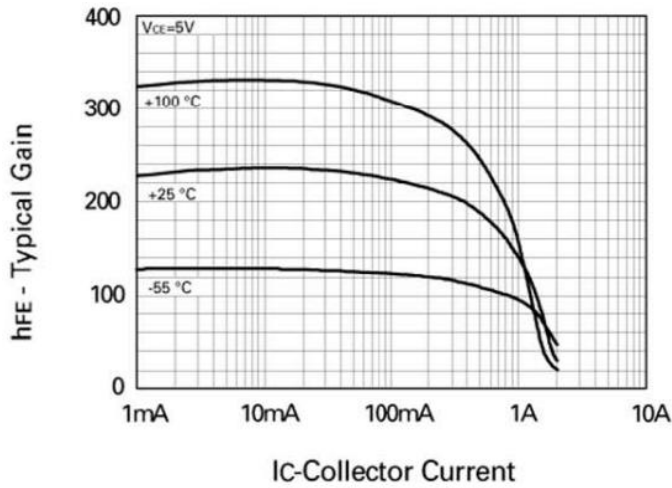
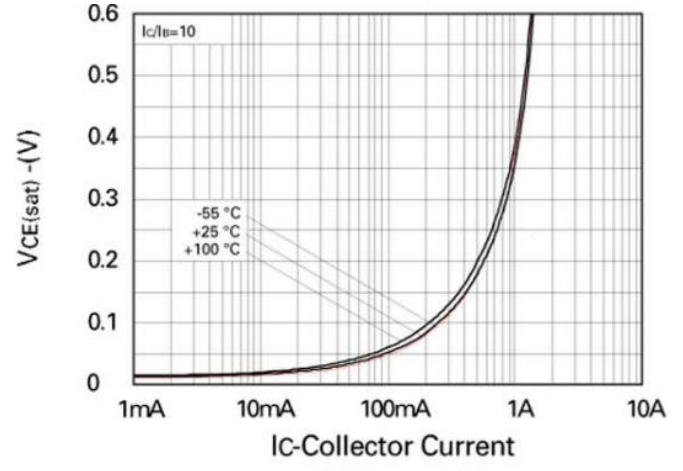
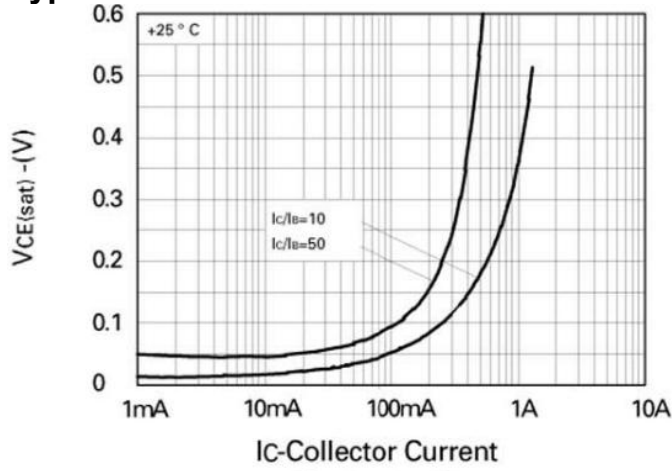
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CB0}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1	A
P_C	Collector Power Dissipation	500	mW
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -60\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -5\text{V}, I_C = -1\text{mA}$	100		300	
		$V_{CE} = -5\text{V}, I_C = -500\text{mA}$	100			
		$V_{CE} = -5\text{V}, I_C = -1\text{A}$	80			
		$V_{CE} = -5\text{V}, I_C = -2\text{A}$	15			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1\text{A}, I_B = -100\text{mA}$			-0.6	V
Base Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -1\text{A}, I_B = -100\text{mA}$			-1.2	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_C = -50\text{mA}$ $f = 100\text{MHz}$	150			MHz

Typical characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

